

# GaN 90-95 GHz PA

### **Preliminary Datasheet**

### **Product Features**

• Frequency Range: 90-95 GHz

Psat: 0.5 WGain: 14 dBPAE: 15%

Bias: Vd=12V, Id=210 mA

• Chip dimensions: 3.4 x 1.35 x 0.05 mm

### **Primary Applications**

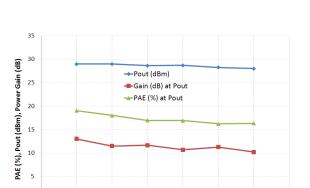
W-band high data rate wireless links

Sensors and Radars

### **Product Description**

The HRL G94-PA is a three stage power amplifier fabricated using HRL's T-gate GaN HEMT process (GaN-on-SiC). The amplifier has independent gate and drain bias for each stage. Front-side bond pads (RF and DC) and backside metallization are Ti/Au, which is compatible with conventional wire and ribbon bonding techniques, and die attach processes.

The G94-PA typically provides 0.5 W output power with 15 dB small signal gain and a PAE of 15% at 92 GHz.



Typical Measured Performance

Vd=12V, Id1=30mA, Id2=60mA, Id3=120mA

Pout at 5 dB compression

## **Electrical Specifications**

Vd=12V, Id1=36mA, Id2=70mA, Id3=144mA

Specification	Min	Тур	Max	Unit
Frequency	90		95	GHz
Linear Gain	13	14	16	dB
Input Return Loss		8		dB
Output Return Loss		6		dB
Saturated Output Power		27		dBm

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## **Absolute Maximum Ratings**

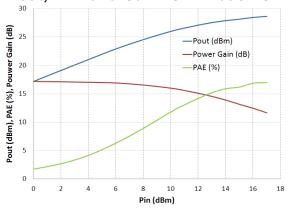
**CW** Operation

Parameter	Rating	Unit
Input Power (Pin)	20	dBm
Drain Voltage (Vd)	12	V
Gate Voltage Range (Vg)	-1 to -3.5	V
Drain Current (Id)	300	mA
Die Attach Temperature (30 sec)	290	°C

Exceeding any one or combination of the Absolute Maximum Ratings may result in permanent damage to the device. Application of Absolute Maximum Ratings on the device for an extended period of time may negatively affect the reliability of the device.

Caution: ESD sensitive device.

#### Pout, PAE and Gain vs. Pin at 92 GHz



### **Outline Drawing**

DC Bond Pads are 0.1mm<sup>2</sup>; Bond pad locations shown from die etch to pad center.

### **Recommended Assembly Diagram**

HRL recommends mounting the die on CuW heat spreader using AuSn eutectic solder.

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